



**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listing, of claims in the application:

**Listing of Claims:**

1. (Original) A fabrication method of a liquid crystal display device, comprising:  
forming a gate line on a substrate by applying a gate photoresist pattern by printing;  
sequentially forming a gate insulating layer, a semiconductor layer, and a high-concentrated N<sup>+</sup> layer over the gate line;  
forming an active region over the high-concentrated N<sup>+</sup> layer by applying an active photoresist pattern by printing;  
forming a conductive layer over the active region;  
depositing a photoresist layer over the conductive layer;  
applying a mask over the photoresist layer, performing a lithography process, and thereby forming a source/drain electrode;  
forming a passivation layer over the source/drain electrode;  
forming a contact hole over the passivation layer by applying a contact hole photoresist pattern by printing; and  
forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist pattern.

2. (Original) The method of claim 1, wherein the mask includes a channel region pattern.

3. (Currently Amended) The method of claim 1, wherein the printing is ~~ink jet printing or~~ roller printing.

4. (Original) The method of claim 1, wherein the step for forming the source/drain electrode comprises:

defining an active layer by sequentially removing the high-concentrated N<sup>+</sup> layer and the semiconductor layer by using the active resist pattern formed by printing as a mask;

removing the active resist pattern;

sequentially forming a conductive layer and a photoresist layer over the active layer;

exposing the photoresist layer, performing a development process, and thereby removing the photoresist layer above a channel region by using the mask including the channel region pattern; and

sequentially removing the conductive layer and the high-concentrated N<sup>+</sup> layer above the channel region.

5-14. (Cancelled)

15. (Currently Amended) The method of claim 1, wherein ~~in the step of applying the~~ mask applied over the photoresist layer in the step of applying the mask, ~~is the only one mask~~ applied is used through out the method of claim 1.

16. (New) The method of claim 1, wherein the printing is ink jet printing.

17. (New) A method for forming a liquid crystal display device, comprising:

forming a gate line on a substrate;

forming a gate insulating layer, a semiconductor layer, and an impurity-doped layer over the gate line;

forming an active region over the impurity-doped layer;

forming a source electrode and a drain electrode over the active region;

forming a passivation layer over the source and drain electrodes;

forming a contact hole over the passivation layer by applying a contact hole photoresist pattern by printing; and

forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist pattern.

18. (New) The method of claim 17, wherein the step of forming the gate line includes applying a gate photoresist pattern on the substrate by printing.

19. (New) The method of claim 17, wherein the step of forming the active region includes applying an active photoresist pattern over the impurity-doped layer by printing.

20. (New) The method of claim 17, wherein the step of forming the source and drain electrodes include:

forming a conductive layer over the active region;

depositing a photoresist layer over the conductive layer;

applying a mask over the photoresist layer, patterning the photoresist layer using the mask, and thereby forming the source and drain electrodes using the patterned photoresist layer.

21. (New) The method of claim 20, wherein the mask applied over the photoresist layer in the step of applying the mask is the only mask applied through out the method of claim 17.

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